

BUK655R0-75C

N-channel TrenchMOS FET

Rev. 01 — 6 July 2010

Objective data sheet

1. Product profile

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for thermally demanding environments due to 175 °C rating
- Suitable for intermediate level gate drive sources

1.3 Applications

- 12 V, 24 V and 42 V Automotive systems
- Motors, lamps and solenoid control
- Automotive DC-DC converter
- Ultra high performance power switching
- Engine management

1.4 Quick reference data

Table 1. Quick reference data

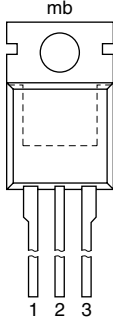
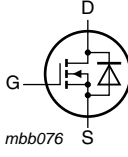
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	-	75	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1	[1]	-	100	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	262	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$; $I_D = 25\text{ A}$; $T_j = 25\text{ °C}$; see Figure 5	-	4.3	5	m Ω
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100\text{ A}$; $V_{sup} \leq 75\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped	-	-	398	mJ

[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	Drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK655R0-75C	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

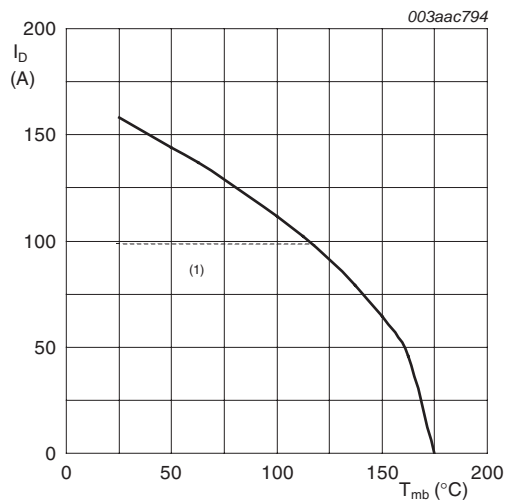
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	75	V
V_{GS}	gate-source voltage		-20	-	20	V
I_D	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see Figure 1 ^[1]	-	-	100	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 10\text{ V};$ see Figure 1 ^[1]	-	-	100	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}; t_p \leq 10\text{ }\mu\text{s};$ pulsed	-	-	633	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ see Figure 2	-	-	262	W
T_{stg}	storage temperature		-55	-	175	°C
T_j	junction temperature		-55	-	175	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$ ^[1]	-	-	100	A
I_{SM}	peak source current	$t_p \leq 10\text{ }\mu\text{s};$ pulsed; $T_{mb} = 25\text{ °C}$	-	-	633	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 100\text{ A}; V_{sup} \leq 75\text{ V}; R_{GS} = 50\text{ }\Omega;$ $V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C};$ unclamped	-	-	398	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy		^{[2][3][4]}	-	-	J

[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

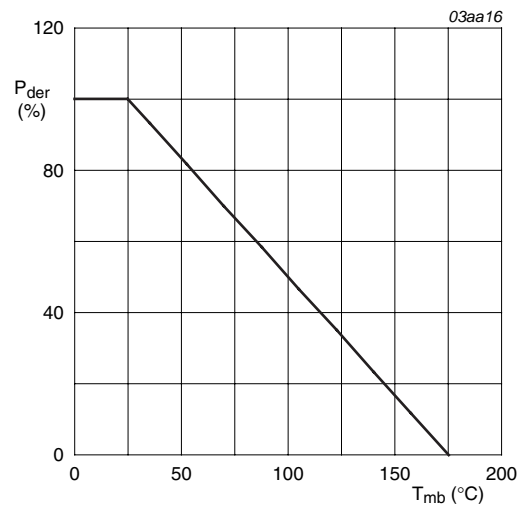
[3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[4] Refer to application note AN10273 for further information.



$V_{GS} \geq 10V$
 (1) Capped at 100 A due to package.

Fig. 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig. 2. Normalized total power dissipation as a function of mounting base temperature

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 3	-	-	0.57	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

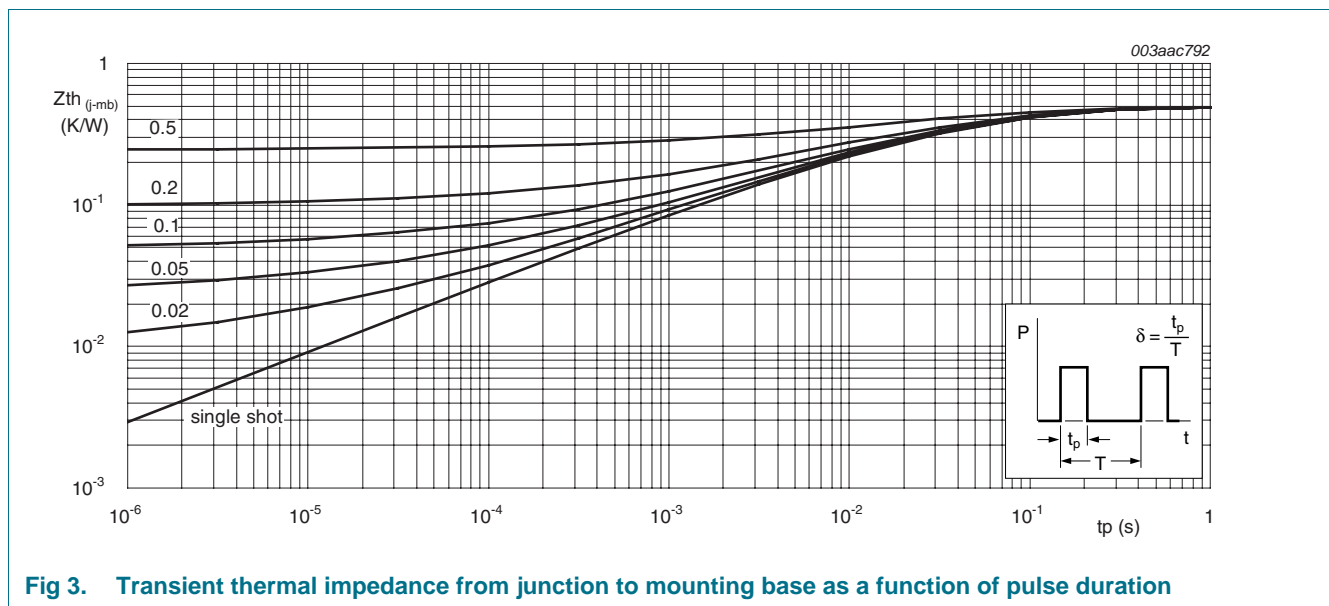


Fig 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

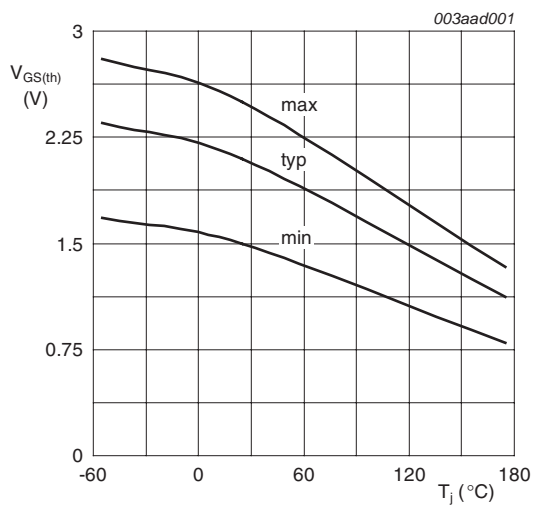
6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	75	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	70	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 4	1.5	2.1	2.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 4	-	-	2.8	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 4	0.8	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	μA
		$V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.02	1	μA
I_{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 5	-	4.3	5	m Ω
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 5	-	[tbd]	[tbd]	m Ω
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 5	-	[tbd]	[tbd]	m Ω
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 5	-	-	10.5	m Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 60 \text{ V}; V_{GS} = 10 \text{ V}$	-	[tbd]	[tbd]	nC
		$I_D = 25 \text{ A}; V_{DS} = 60 \text{ V}; V_{GS} = 5 \text{ V}$	-	[tbd]	[tbd]	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 60 \text{ V}; V_{GS} = 10 \text{ V}$	-	[tbd]	[tbd]	nC
Q_{GD}	gate-drain charge		-	[tbd]	[tbd]	nC
C_{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C}$	-	[tbd]	[tbd]	pF
C_{oss}	output capacitance		-	[tbd]	[tbd]	pF
C_{riss}	reverse transfer capacitance		-	[tbd]	[tbd]	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 10 \text{ } \Omega$	-	[tbd]	[tbd]	ns
t_r	rise time		-	[tbd]	[tbd]	ns
$t_{d(off)}$	turn-off delay time		-	[tbd]	[tbd]	ns
t_f	fall time		-	[tbd]	[tbd]	ns
L_D	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	4.5	-	nH
		from contact screw on mounting base to centre of die ; $T_j = 25 \text{ }^\circ\text{C}$	-	3.5	-	nH
L_S	internal source inductance	from source lead to source bond pad ; $T_j = 25 \text{ }^\circ\text{C}$	-	7.5	-	nH

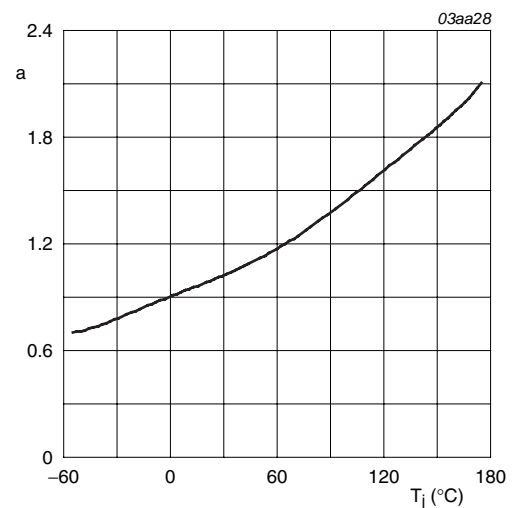
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20 \text{ A}; di_S/dt = -100 \text{ A}/\mu\text{s};$	-	[tbd]	[tbd]	ns
Q_r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}$	-	[tbd]	[tbd]	nC



$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

Fig 4. Gate-source threshold voltage as a function of junction temperature



$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 5. Normalized drain-source on-state resistance factor as a function of junction temperature

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

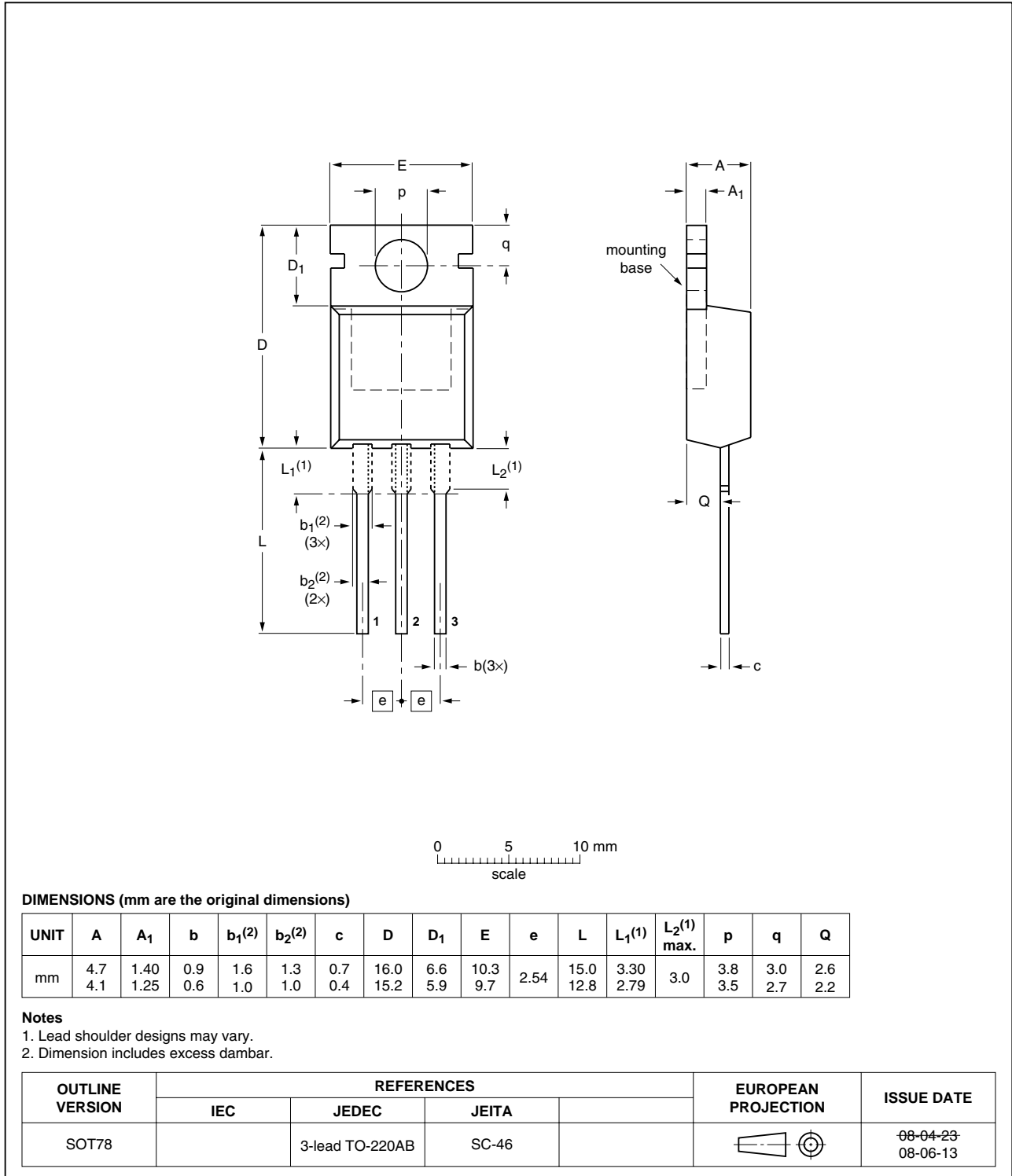


Fig 6. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK655R0-75C v.1	20100706	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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11. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	3
5	Thermal characteristics	5
6	Characteristics	6
7	Package outline	8
8	Revision history	9
9	Legal information	10
9.1	Data sheet status	10
9.2	Definitions	10
9.3	Disclaimers	10
9.4	Trademarks	11
10	Contact information	11

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